

描述 / Descriptions

PDFN3×3-8L 塑封封装双 N 沟道 MOS 场效应管。

Double N-CHANNEL MOSFET in a PDFN3×3-8L Plastic Package.

特征 / Features

$V_{DS} (V) = 30V$

$I_D = 24A (V_{GS} = \pm 20V)$

$R_{DS(ON)} @ 10V \leq 14m\Omega (Typ. 12m\Omega)$

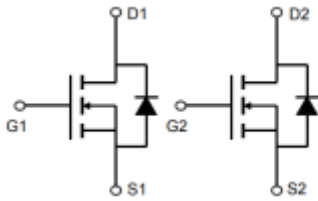
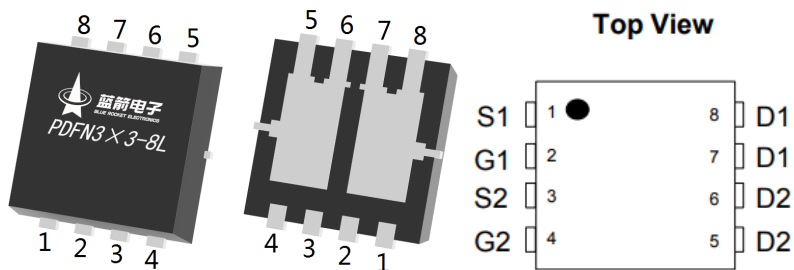
符合 AEC-Q101 标准高可靠性要求，无卤产品。

Qualified to AEC-Q101 Standards for High Reliability, HF Product.

用途 / Applications

用作一般的开关和相位控制，满足汽车应用的严格要求。

Intended for use in general purpose switching and phase control applications, Meet the stringent requirements of automotive applications.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning****印章代码 / Marking**

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25^{\circ}\text{C})$	24	A
Drain Current - Pulsed		I_{DM}	55	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy		E_{AS}	199	mJ
Avalanche Current		I_{AS}	12.9	A
Power Dissipation		$P_D(T_c=25^{\circ}\text{C})$	15.5	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Junction-to-Ambient	$t \leq 10$	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$
Junction-to-Ambient	Steady-State		75	
Junction-to-Case	Steady-State	$R_{\theta JC}$	9	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.8	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		12	14	$m\Omega$
		$V_{GS}=4.5V$ $I_D=10A$		23	30	$m\Omega$
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		666		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			63		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.7		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=8A$		13.6		nC
Total Gate Charge	$Q_{g(4.5V)}$			6.8		
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=1.87\Omega$ $R_{GEN}=4.5\Omega$		5		ns
Turn-On Rise Time	t_r			3.5		
Turn-Off Delay Time	$t_{d(off)}$			22		
Turn-Off Fall Time	t_f			4.5		

电参数曲线图 / Electrical Characteristic Curve

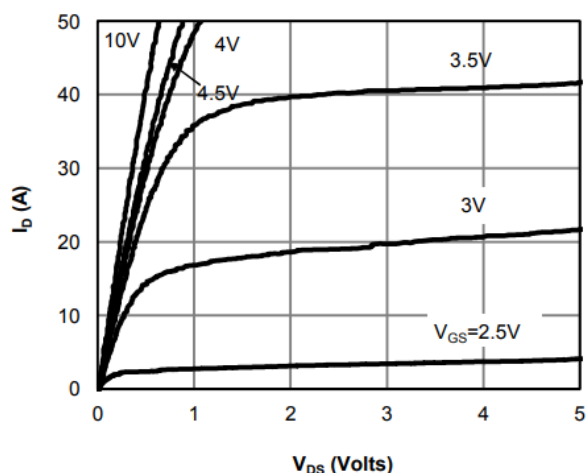


Figure 1: On-Region Characteristics

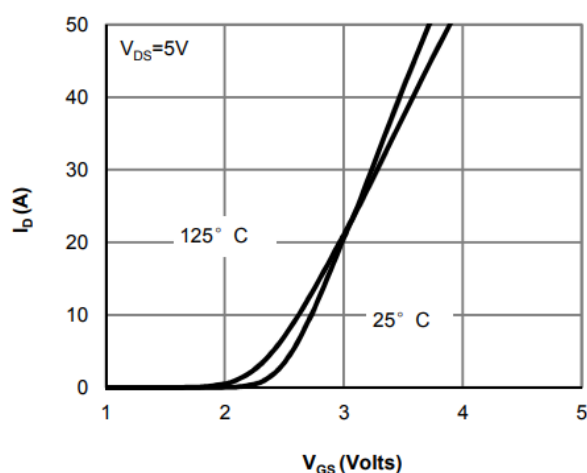


Figure 2: Transfer Characteristics

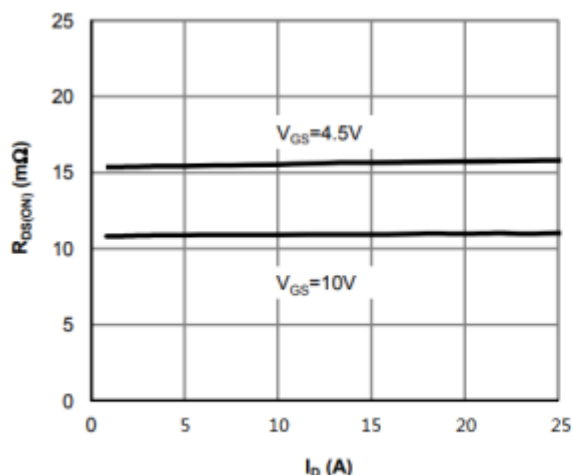


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

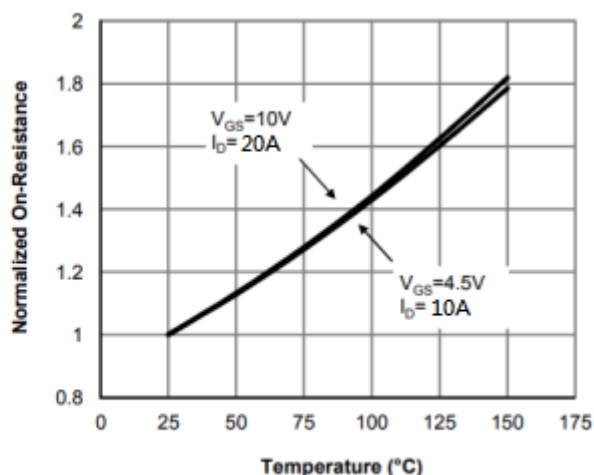


Figure 4: On-Resistance vs. Junction Temperature

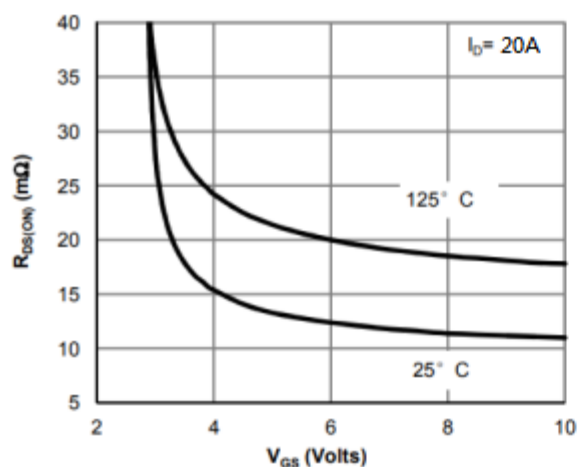


Figure 5: On-Resistance vs. Gate-Source Voltage

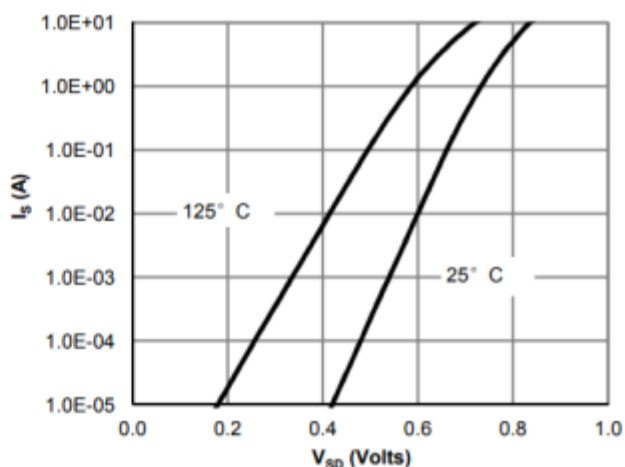
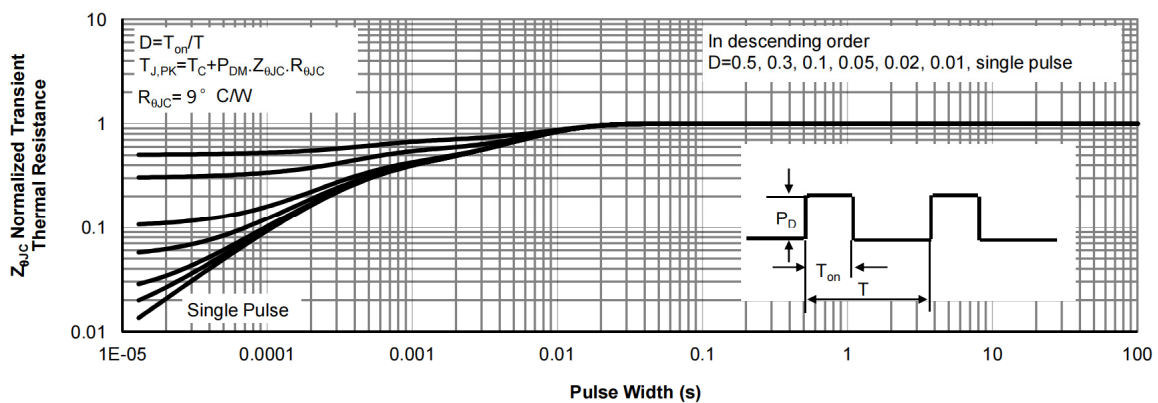
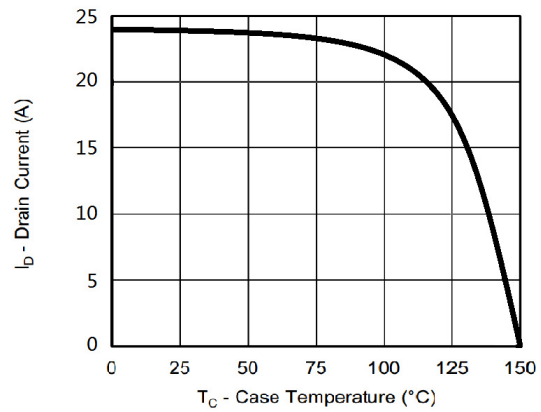
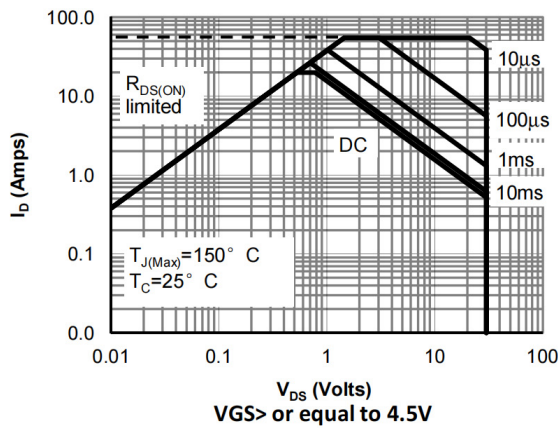
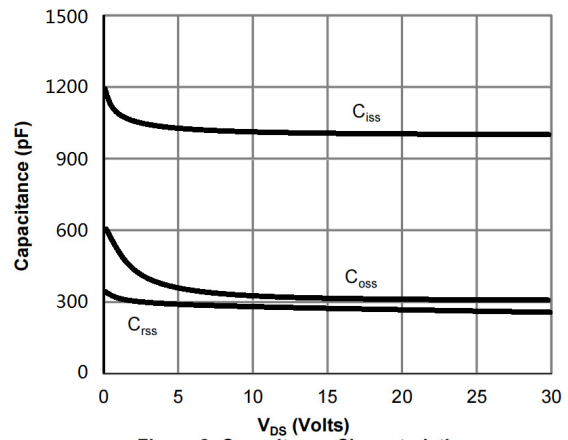
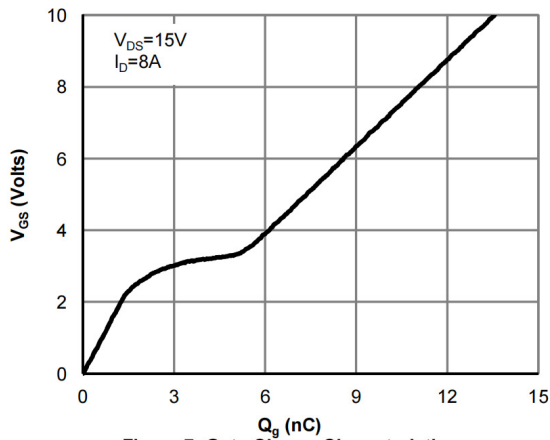
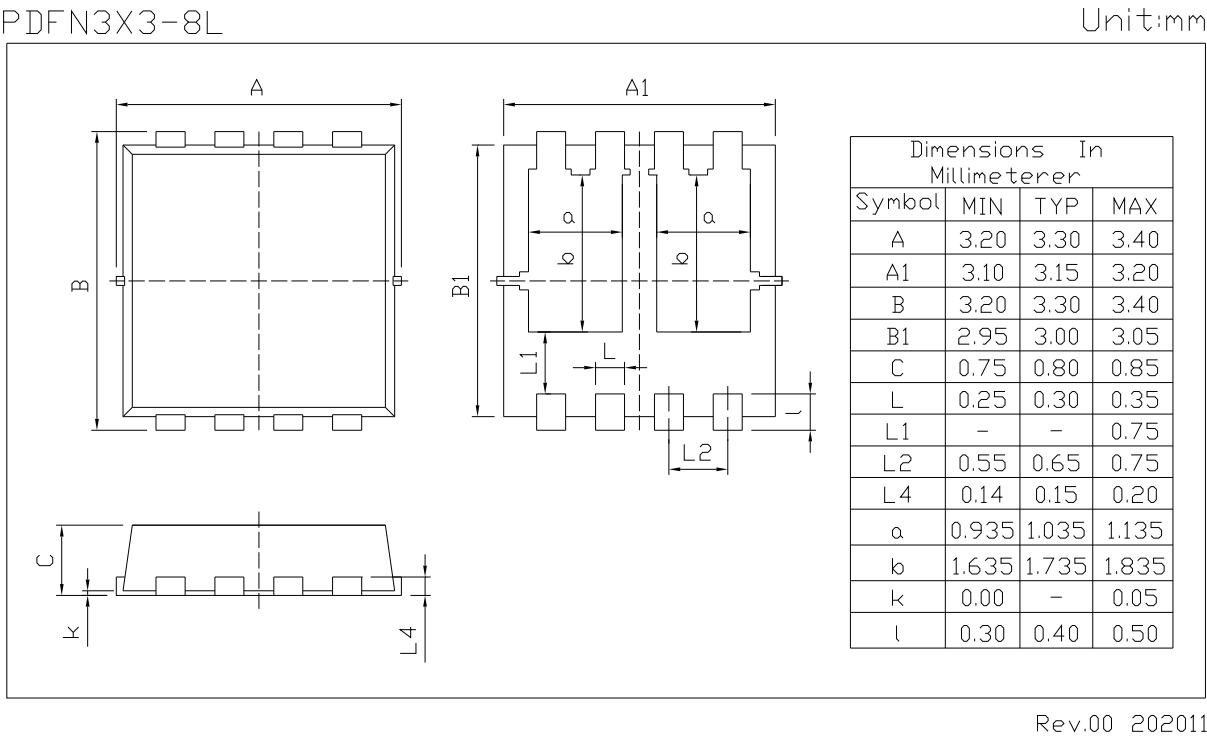


Figure 6: Body-Diode Characteristics

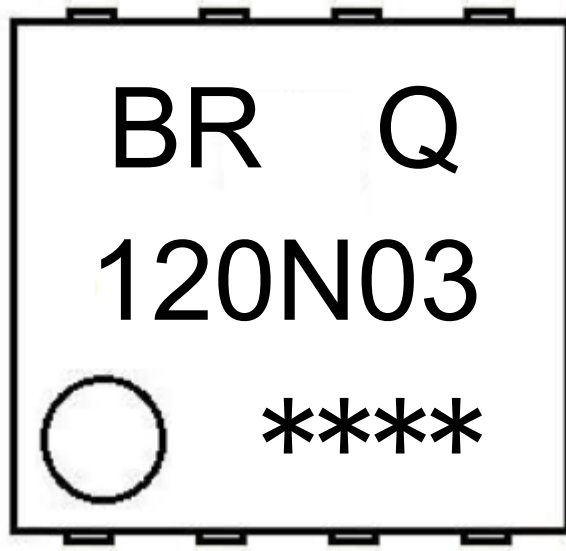
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions



印章说明 / Marking Instructions



说明：

BR： 为公司代码

Q： 为汽车无卤产品标识

120N03： 为型号代码

*****： 为生产批号代码，随生产批号变化

Note:

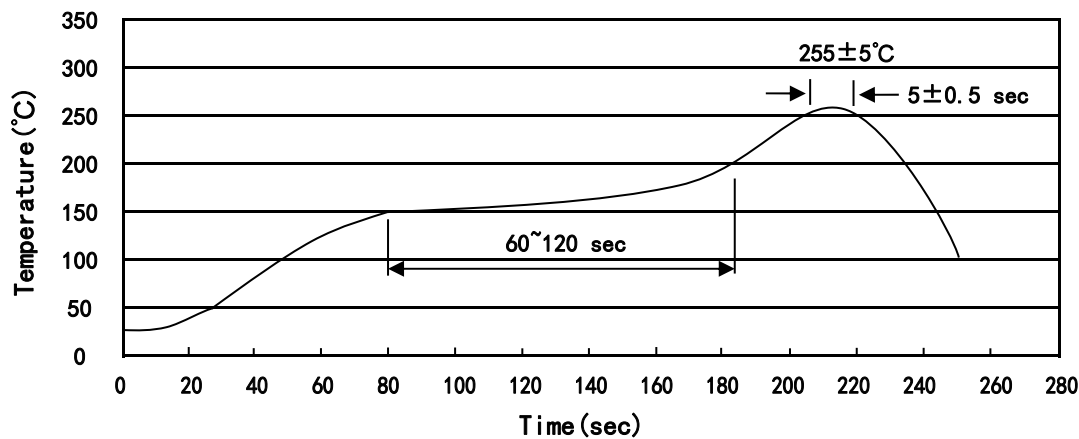
BR: Company Code

Q: Automobile halogen-free product Code

120N03: Product Type Code

*****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



- 说明 :
1、预热温度 150 ~ 200℃ , 时间 60 ~ 120sec;
2、峰值温度 255±5℃ , 时间持续为 5±0.5sec;
3、焊接制程冷却速度为 2 ~ 10℃/sec.
- Note:
1.Preheating:150~200℃, Time:60~120sec.
2.Peak Temp.:255±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度 : 260±5℃ 时间 : 10±1 sec. Temp.:260±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN3×3-8L	5,000	2	10,000	6	60,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices